/ Descriptions

TO-251 ĮĮĿ N ŝ MOS ĵ ŵ Ẓ ˥

N-CHANNEL MOSFET in a TO-251 Plastic Package.

/ Features

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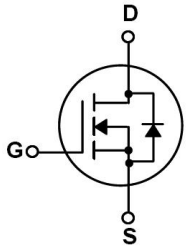
Low gate charge, low crss, fast switching.

/ Applications

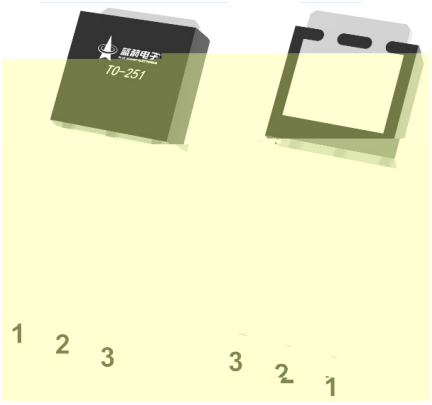
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These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 χ G PIN 2 χ D PIN 3 χ S

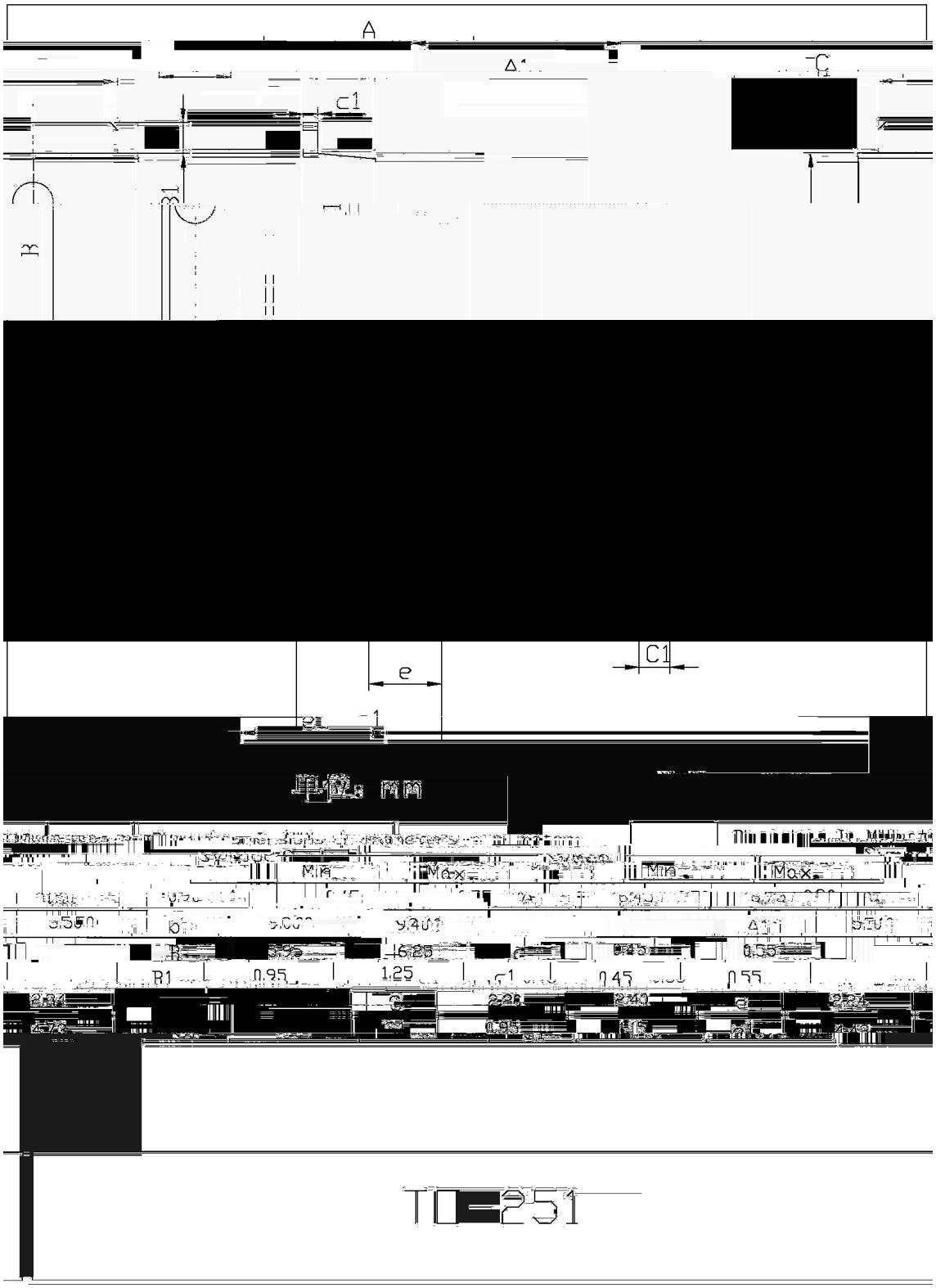
/ Marking

ð м ٦ ب ″ See Marking Instructions.

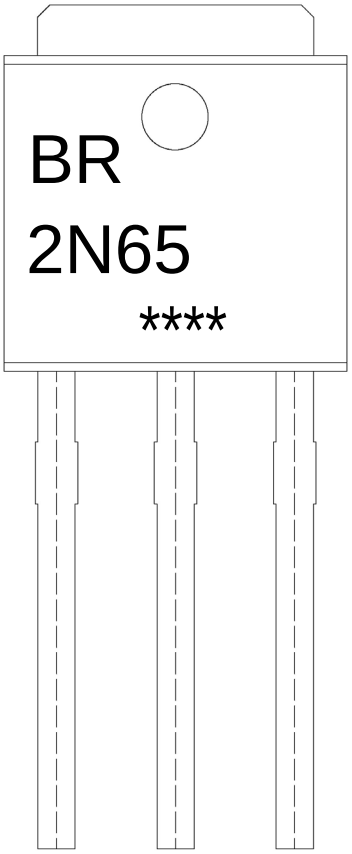
v ‴Ω Parameter	ϒ N Symbol	‴Ω Ö Rating	D Ч Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	I_D(Tc=25)	2.0	A
Drain Current	I_D(Tc=100)	1.3	A
Drain Current - Pulsed	I_{DM}	8	A
Gate-Source Voltage	V_{GS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	120	mJ
Repetitive Avalanche Energy	E_{AR}	5.4	mJ
Avalanche Current	I_{AR}	2.0	A
Power Dissipation	P_D(Tc=25)	28	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	
Junction to Ambient	$R_{\theta JA}$	110	/W
Junction to Case	$R_{\theta JC}$	4.46	/W

BRI2N65

/ Package Dimensions



/ Marking Instructions



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5Q98 χ	ѭ ҙ N Ґђ
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Note:

BR:	Company Code
2N65:	Product Type
****:	Lot No. Code, code change with Lot No